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C. Risko
School of Chemistry and Biochemistry, Georgia Institute of Technology, Atlanta, Georgia 30332-0400

G. P. Kushto and Z. H. Kafafi
Optical Sciences Division, U.S. Naval Research Laboratory, Washington, DC 20375

J. L. Brédas
School of Chemistry and Biochemistry, Georgia Institute of Technology, Atlanta, Georgia 30332-0400

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The third author’s name was misspelled in the original article. The correct spelling is Z. H. Kafafi.